

74HC245

Octal 3-State Noninverting Bus Transceiver

High-Performance Silicon-Gate CMOS

The 74HC245 is identical in pinout to the LS245. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

The HC245 is a 3-state noninverting transceiver that is used for 2-way asynchronous communication between data buses. The device has an active-low Output Enable pin, which is used to place the I/O ports into high-impedance states. The Direction control determines whether data flows from A to B or from B to A.

Features

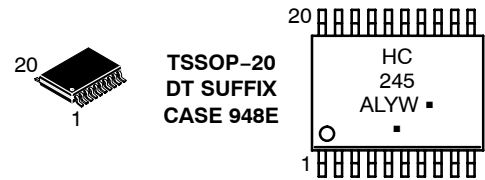
- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 308 FETs or 77 Equivalent Gates
- This is a Pb-Free Device



ON Semiconductor®

<http://onsemi.com>

MARKING DIAGRAMS



HC245 = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

74HC245

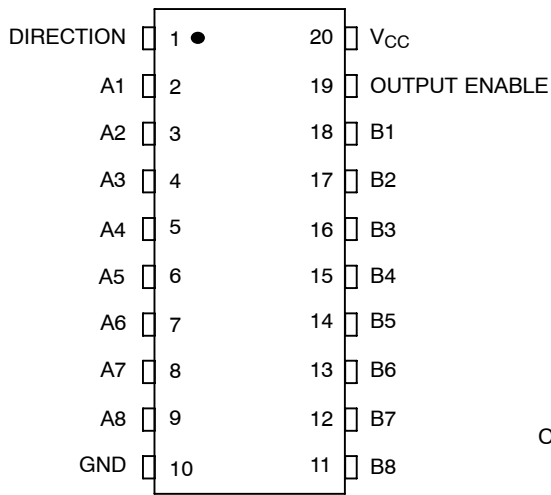


Figure 1. Pin Assignment

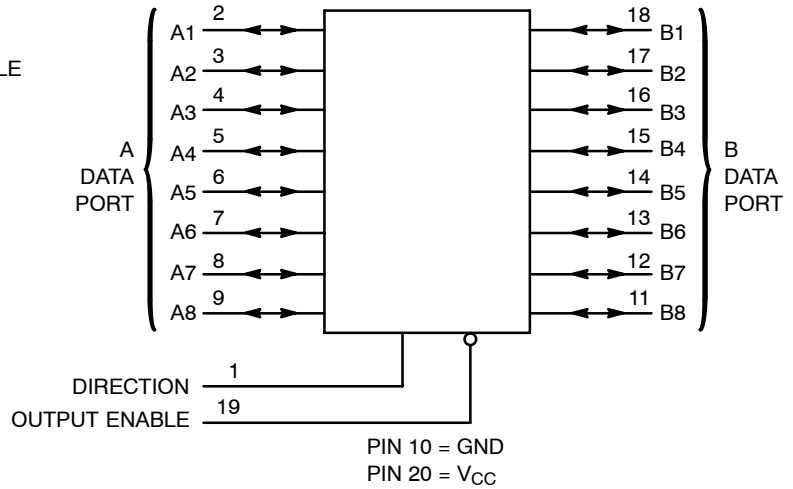


Figure 2. Logic Diagram

FUNCTION TABLE

| Control Inputs | | Operation |
|----------------|-----------|---------------------------------------|
| Output Enable | Direction | |
| L | L | Data Transmitted from Bus B to Bus A |
| L | H | Data Transmitted from Bus A to Bus B |
| H | X | Buses Isolated (High-Impedance State) |

X = don't care

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------------|-----------|-----------------------|
| 74HC245DTR2G | TSSOP-20* | 2500 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

74HC245

MAXIMUM RATINGS (Note 1)

| Symbol | Parameter | Value | Unit |
|----------------------|---|-------------------------------|------|
| V _{CC} | DC Supply Voltage | -0.5 to +7.0 | V |
| V _{IN} | DC Input Voltage | -0.5 to V _{CC} + 0.5 | V |
| V _{OUT} | DC Output Voltage (Note 2) | -0.5 to V _{CC} + 0.5 | V |
| I _{IK} | DC Input Diode Current | ±20 | mA |
| I _{OK} | DC Output Diode Current | ±35 | mA |
| I _{OUT} | DC Output Sink Current | ±35 | mA |
| I _{CC} | DC Supply Current per Supply Pin | ±75 | mA |
| I _{GND} | DC Ground Current per Ground Pin | ±75 | mA |
| T _{STG} | Storage Temperature Range | -65 to +150 | °C |
| T _L | Lead Temperature, 1 mm from Case for 10 Seconds | 260 | °C |
| T _J | Junction Temperature Under Bias | +150 | °C |
| θ _{JA} | Thermal Resistance TSSOP | 128 | °C/W |
| P _D | Power Dissipation in Still Air at 85°C TSSOP | 450 | mW |
| MSL | Moisture Sensitivity | Level 1 | |
| F _R | Flammability Rating Oxygen Index: 30% to 35% | UL 94 V-0 @ 0.125 in | |
| V _{ESD} | ESD Withstand Voltage Human Body Model (Note 3) Machine Model (Note 4) | >2000 >200 | V |
| I _{LATCHUP} | Latchup Performance Above V _{CC} and Below GND at 85°C (Note 5) | ±300 | mA |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 20 ounce copper trace with no air flow.
2. I_O absolute maximum rating must be observed.
3. Tested to EIA/JESD22-A114-A.
4. Tested to EIA/JESD22-A115-A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit | |
|------------------------------------|--|-------------------------|-----------------|------|----|
| V _{CC} | DC Supply Voltage (Referenced to GND) | 2.0 | 6.0 | V | |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | V _{CC} | V | |
| T _A | Operating Temperature, All Package Types | -55 | +125 | °C | |
| t _r , t _f | Input Rise and Fall Time (Figure 3) | | | | |
| | | V _{CC} = 2.0 V | 0 | 1000 | ns |
| | | V _{CC} = 4.5 V | 0 | 500 | |
| | | V _{CC} = 6.0 V | 0 | 400 | |

74HC245

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| Symbol | Parameter | Test Conditions | V _{CC} V | Guaranteed Limit | | | Unit |
|-----------------|--|---|--------------------------|---------------------------|---------------------------|---------------------------|------|
| | | | | -55 to 25°C | ≤ 85°C | ≤ 125°C | |
| V _{IH} | Minimum High-Level Input Voltage | V _{out} = V _{CC} - 0.1 V I _{out} ≤ 20 μA | 2.0 3.0 4.5 6.0 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | V |
| V _{IL} | Maximum Low-Level Input Voltage | V _{out} = 0.1 V I _{out} ≤ 20 μA | 2.0 3.0 4.5 6.0 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | V |
| V _{OH} | Minimum High-Level Output Voltage | V _{in} = V _{IH} I _{out} ≤ 20 μA | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | V _{in} = V _{IH} I _{out} ≤ 2.4 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA | 3.0 4.5 6.0 | 2.48 3.98 5.48 | 2.34 3.84 5.34 | 2.2 3.7 5.2 | |
| V _{OL} | Maximum Low-Level Output Voltage | V _{in} = V _{IL} I _{out} ≤ 20 μA | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | V _{in} = V _{IL} I _{out} ≤ 2.4 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA | 3.0 4.5 6.0 | 0.26 0.26 0.26 | 0.33 0.33 0.33 | 0.4 0.4 0.4 | |
| I _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND | 6.0 | ±0.1 | ±1.0 | ±1.0 | μA |
| I _{OZ} | Maximum Three-State Leakage Current | Output in High-Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND | 6.0 | ±0.5 | ±5.0 | ±10 | μA |
| I _{CC} | Maximum Quiescent Supply Current (per Package) | V _{in} = V _{CC} or GND I _{out} = 0 μA | 6.0 | 4.0 | 40 | 40 | μA |

6. Information on typical parametric values and high frequency or heavy load considerations can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

| Symbol | Parameter | V _{CC} V | Guaranteed Limit | | | Unit |
|--|---|----------------------|------------------|--------|---------|------|
| | | | -55 to 25°C | ≤ 85°C | ≤ 125°C | |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, A to B, B to A (Figures 1 and 3) | 2.0 | 75 | 95 | 110 | ns |
| | | 3.0 | 55 | 70 | 80 | |
| | | 4.5 | 15 | 19 | 22 | |
| | | 6.0 | 13 | 16 | 19 | |
| t _{PLZ} , t _{PHZ} | Maximum Propagation Delay, Direction or Output Enable to A or B (Figures 2 and 4) | 2.0 | 110 | 140 | 165 | ns |
| | | 3.0 | 90 | 110 | 130 | |
| | | 4.5 | 22 | 28 | 33 | |
| | | 6.0 | 19 | 24 | 28 | |
| t _{PZL} , t _{PZH} | Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4) | 2.0 | 110 | 140 | 165 | ns |
| | | 3.0 | 90 | 110 | 130 | |
| | | 4.5 | 22 | 28 | 33 | |
| | | 6.0 | 19 | 24 | 28 | |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 1 and 3) | 2.0 | 60 | 75 | 90 | ns |
| | | 3.0 | 23 | 27 | 32 | |
| | | 4.5 | 12 | 15 | 18 | |
| | | 6.0 | 10 | 13 | 15 | |
| C _{in} | Maximum Input Capacitance (Pin 1 or Pin 19) | - | 10 | 10 | 10 | pF |
| C _{out} | Maximum Three-State I/O Capacitance (I/O in High-Impedance State) | - | 15 | 15 | 15 | pF |

7. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

| C _{PD} | Power Dissipation Capacitance (Per Transceiver Channel) (Note 8) | Typical @ 25°C, V _{CC} = 5.0 V | | pF |
|-----------------|--|---|--|----|
| | | 40 | | |
| | | | | |

8. Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

74HC245

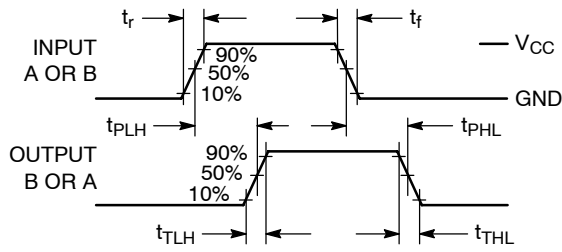


Figure 3. Switching Waveform

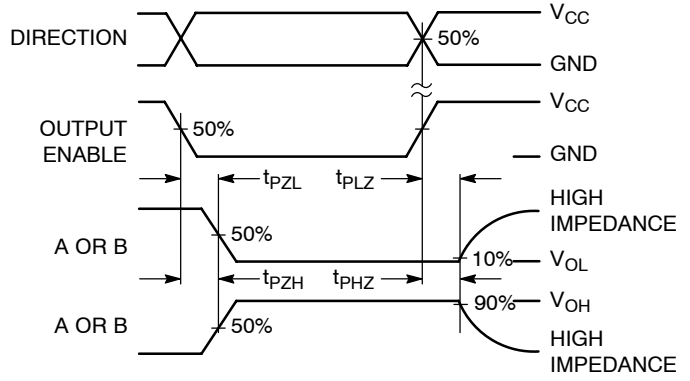
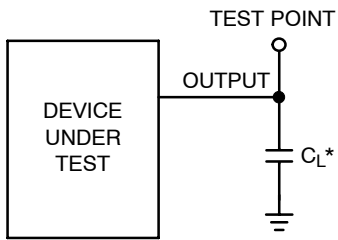
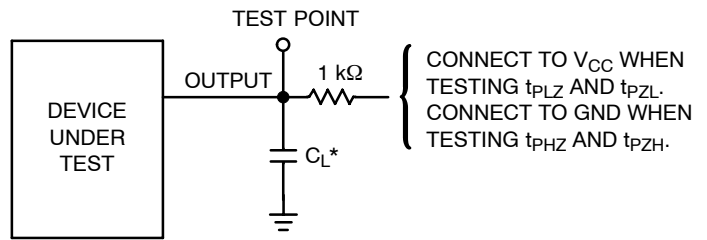


Figure 4. Switching Waveform



*Includes all probe and jig capacitance

Figure 5. Test Circuit



*Includes all probe and jig capacitance

Figure 6. Test Circuit

74HC245

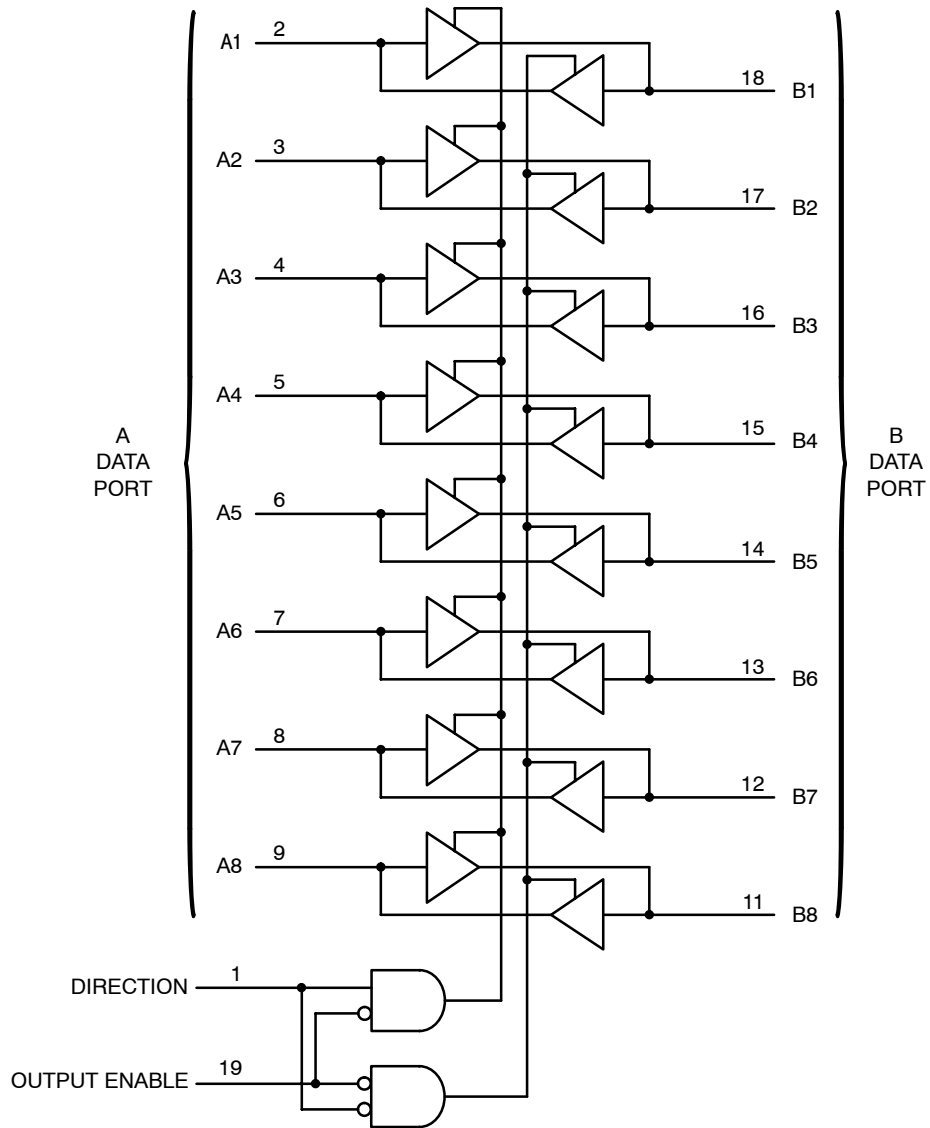
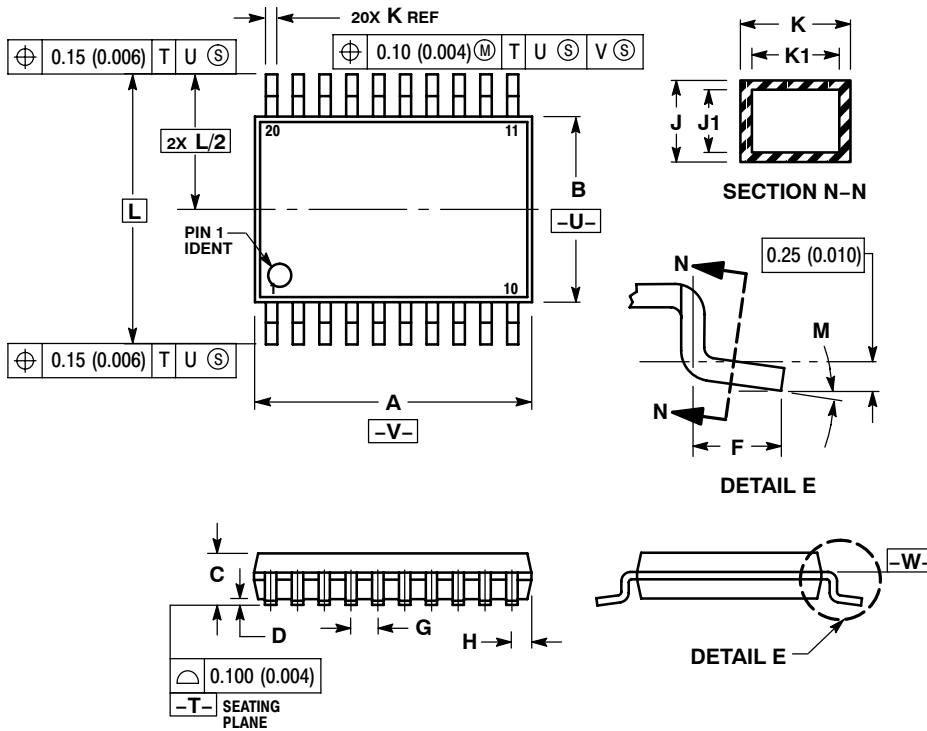


Figure 7. Expanded Logic Diagram

74HC245

PACKAGE DIMENSIONS

TSSOP-20
CASE 948E-02
ISSUE C

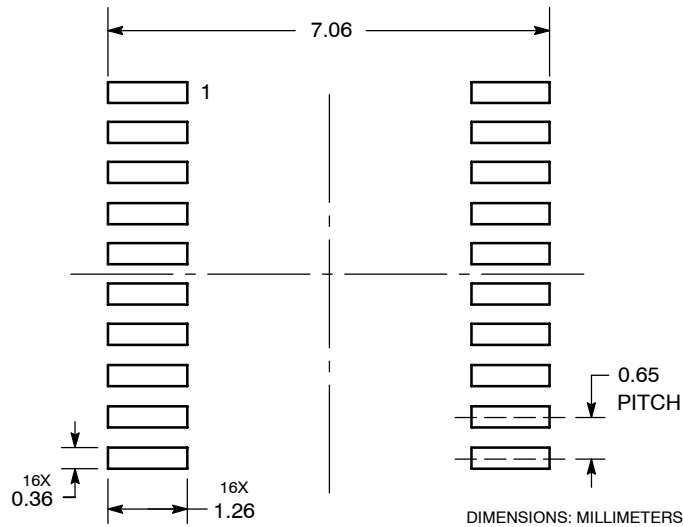


NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 6.40 | 6.60 | 0.252 | 0.260 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| C | --- | 1.20 | --- | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 BSC | | 0.026 BSC | |
| H | 0.27 | 0.37 | 0.011 | 0.015 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 BSC | | 0.252 BSC | |
| M | 0° | 8° | 0° | 8° |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.